carrier density within the dendrites which perturb the current stream lines and may either enhance or decrease $(\Delta R/R_0)$ in accordance with the considerations summarized by Beer.[8] The temperature dependence of the magnetoresistance coefficient in a fixed magnetic field of 10 kOe is shown in Fig. 2. It may be expressed as:

$$\frac{\partial}{\partial T}(\Delta R/R_0) = \frac{w}{l_d} \cdot H \cdot \frac{\partial \mu_n}{\partial T} \qquad (2)$$

The peak in the $(\Delta R/R_0)$ vs T curve near 300°K is an anomaly. It does not appear in the temperature dependence of bulk n-type InSb which increases monotonically with T to 100°K. It is however in qualitative agreement with the μ_n vs T dependence[9] of single-phase InSb films which has been attributed to a combination of lattice and dislocation scattering in accordance with the model of Dexter and Seitz.[10]

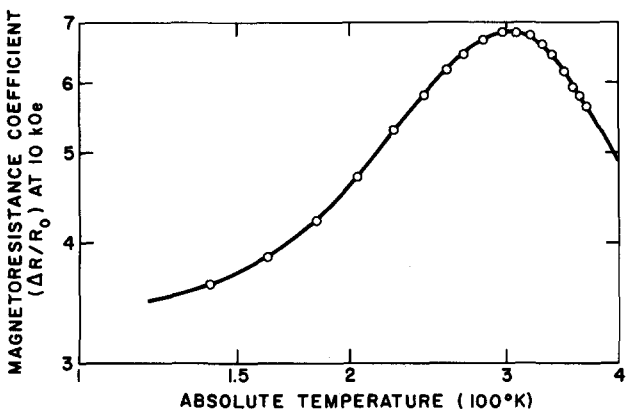

Fig. 2. Magnetoresistance coefficient of same film as a function of the absolute temperature and a fixed magnetic field. Curve illustrates temperature dependence of the electron mobility.

The magnetoresistance coefficients of InSb films with an ordered dendrite structure, such as shown in Fig. 1, are the highest reported thus far in semiconductor films. Larger $(\Delta R/R_0)$ values are anticipated with an improvement (presently under way) in controlling the temperature gradients and their time derivative during the crystallization process.

[1]H. H. Wieder and A. R. Clawson, *Proc. Intern. Conf. Physics of Semiconductors,* Paris, pp. 1155–1159 (1964).
[2]H. H. Wieder and A. R. Clawson, *Solid-State Electron.* **8,** 467 (1965).
[3]H. H. Wieder, *Solid-State Commun.* **3,** 159 (1965).
[4]The measured Hall voltage was properly corrected for the geometrical, (l/w) dependence and the Hall angle. [R. F. Wick, *J. Appl. Phys.* **25,** 741 (1954)]. It was not corrected for the finite size of the Hall electrodes, [S. K. Datta and A. N. Daw, *Z. Naturforsch.* **19a,** 392 (1964)].
[5]H. J. Lippmann and F. Kuhrt, *Z. Naturforsch.* **13,** 462 (1958).
[6]H. Weiss, *J. Appl. Phys.* **32,** 2064 (1961).
[7]C. H. Champness, *Can. J. Phys.* **41,** 890 (1963).
[8]A. C. Beer, *Galvonomagnetic Effects in Semiconductors,* (Academic Press, 1963), Ch. X.
[9]H. H. Wieder, *Proc. IEEE–NASA,* Hall Effect Conf. Nov., 1964, (*Solid-State Electron.,* in press).
[10]D. L. Dexter and F. Seitz, *Phys. Rev.* **86,** 964 (1952).

ERRATA

In "Holograms with Nonpseudoscopic Real Images," [*Appl. Phys. Letters* **8,** 146 (1966)], F. B. Rotz and A. A. Friesem, Institute of Science and Technology, The University of Michigan, Ann Arbor, Michigan, the abstract should read as follows: ("real image" subject for second hologram; pseudoscopy = reversed relief; E).

The title of the paper by S. M. Jarrett, J. Nuñez, and G. Gould [*Appl. Phys. Letters* **8,** 150 (1966)], TRG Incorporated, A Subsidiary of Control Data Corporation, Melville, New York, should read: "Laser Oscillation in Atomic Cl in HCl Gas Discharges."